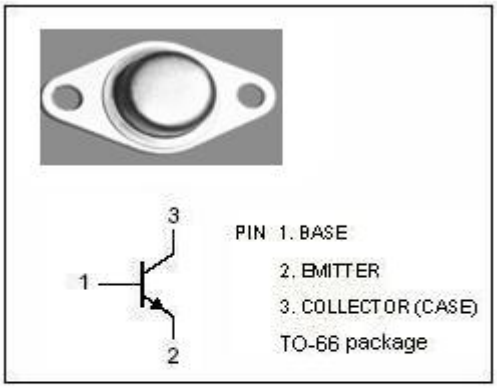
isc Silicon NPN Power Transistor 2SD554

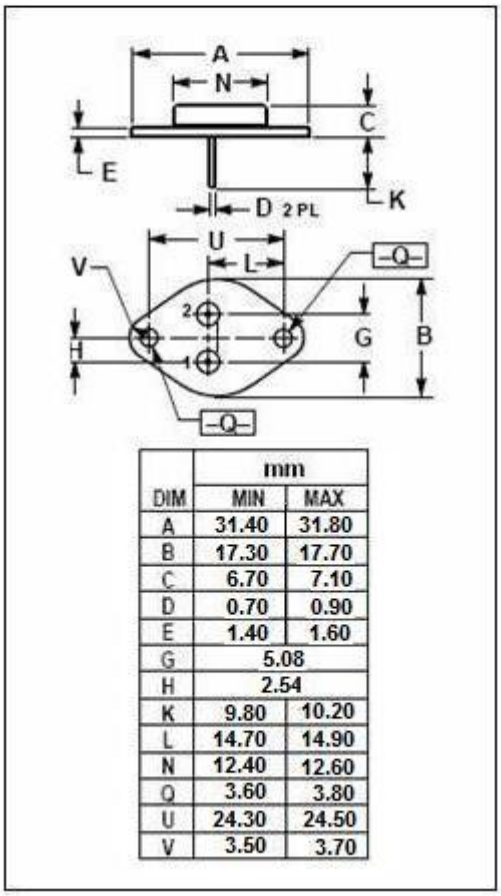
DESCRIPTION

- Contunuous Collector Current-I_C= 2A
- Power Dissipation-P_D=30W @T_C= 25℃
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 2.0 V(Max)@ I_C = 1A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for high-speed switching and linear amplifier application for high-voltage operational amplifiers, switching regulators, converters,deflection stages and high fidelity amplifiers.



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	250	V
V_{CEO}	Collector-Emitter Voltage	250	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	2.0	A
I_{CM}	Collector Current-Peak	5.0	A
I_B	Base Current	1.0	A
P_C	Collector Power Dissipation@T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA ; I_B= 0	250		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1A; I_B= 0.1A		2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 1A; I_B= 0.1A		1.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 250V; I_B= 0		1.0	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= 250V; I_E= 0		0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C=0		0.1	mA
h_{FE-1}	DC Current Gain	I_C= 0.3A ; V_{CE}= 5V	60		
h_{FE-2}	DC Current Gain	I_C= 1A ; V_{CE}= 5V	10	150	